Docket No.: 5287-0101PUS1

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0138] with the following amended paragraph:

[0138]

Working Example 8

As shown in FIG. 12a, the semiconductor element in this working example is formed in the same matter as in Working Example 7, except that a nickel film [[65d]] 65a whose thickest region is about 5 Å is formed in island form over the p-type semiconductor layers, and over this a multilayer film consisting of an upper platinum film [[65c]] 65d, a middle nickel film [[65b]] 65c, and a lower silver film [[65a]] 65b is formed as a first metal film 65.